

**In the Claims:**

Please amend claims 6, 10, 11, 17, and 26, and add new claims 29-61 as follows:

1. (Original) A method of evaluating a processing chamber, comprising:  
performing a substrate processing operation and a process perturbation operation in a process chamber;  
collecting optical emission spectroscopy (OES) data and radio frequency (RF) data during the substrate processing operation and the process perturbation operations; and  
performing a multivariate analysis on the collected OES and RF data from the process chamber.
2. (Original) The method of claim 1, wherein the multivariate analysis comprises principle component analysis (PCA).
3. (Original) The method of claim 2, further comprising:  
determining if the OES and/or RF data need to be manipulated;  
performing the data manipulation; and  
performing a multivariate analysis on the revised OES and RF data from the chamber.
4. (Original) The method of claim 3, wherein steady principle components and transitional principle components are identified for the process chamber by principle component analysis.
5. (Original) The method of claim 3, further comprising:  
using decomposition of an OES and RF data matrix to yield scores of principle components to determine if the OES and/or RF data need to be manipulated.

6. (Currently amended) The method of claim 3, further comprising:  
enhancing [[the]] weak signals either by amplifying post perturbation signals, or by selecting a narrower and more sensitive wavelength range or frequency range.
7. (Original) The method of claim 1, further comprising:  
using a result of the multivariate analysis to calibrate the process chamber or calibrate another process chamber.
8. (Original) The method of claim 1, further comprising:  
using a result of the multivariate analysis to identify a fault in the process chamber or identify a fault in another process chamber.
9. (Original) A method of evaluating a process chamber, comprising:  
performing a first substrate processing operation and a first process perturbation operation in a reference chamber;  
collecting optical emission spectroscopy (OES) data and radio frequency (RF) data during the first substrate processing operation and the first process perturbation operation;  
performing a first multivariate analysis on the collected OES and RF data from the reference chamber to produce first multivariate analysis results;  
performing a second substrate processing operation and a second process perturbation operation in a process chamber that is under study, where the first process operation and the second process operation are similar, and the first process perturbation operation and the second process perturbation operation are similar;  
collecting OES data and RF data during the second process operation and the second process perturbation operation;  
performing a second multivariate analysis on the collected OES and RF data from the chamber under study to produce second multivariate analysis results; and  
comparing the second multivariate analysis results from the chamber under study to the first multivariate analysis results from the reference chamber.

10. (Currently amended) The method of claim 9 further comprising using a result of [[the]] comparing [[step]] the second multivariate analysis results to the first multivariate analysis results to calibrate the chamber under study.
11. (Currently amended) The method of claim 9, further comprising:  
using a result of [[the]] comparing [[step]] the second multivariate analysis results to the first multivariate analysis results to identify a fault in the chamber under study.
12. (Original) The method of claim 9, wherein the first and second multivariate analyses comprise principle component analysis (PCA).
13. (Original) The method of claim 9, further comprising:  
determining if the OES and/or RF data collected from the reference chamber need to be manipulated;  
performing the data manipulation on the data collected from the reference chamber;  
performing a multivariate analysis on the revised OES and RF data from the reference chamber; and  
manipulating the OES and/or RF data collected from the process chamber that is under study according to the data manipulation scheme developed for the reference chamber.
14. (Original) The method of claim 13, wherein steady principle components and transitional principle components are identified for the reference chamber and the chamber under study by principle component analysis.
15. (Original) The method of claim 13, wherein comparing the results from the first and second multivariate analyses further comprises performing an inner product of the identified principle components for the reference chamber and the chamber under study to generate matching scores.

16. (Original) The method of claim 13, further comprising:  
using decomposition of OES and RF data matrixes to yield scores for principle components to determine if the OES and/or RF data need to be manipulated.
17. (Currently amended) The method of claim 13, further comprising:  
enhancing [[the]] weak signals either by amplifying post perturbation signals, or by selecting a narrower and more sensitive wavelength range or frequency range.
18. (Original) The method of claim 9, further comprising:  
comparing the matching scores to a pre-established matching control limit.
19. (Original) The method of claim 9, wherein the amount of process parameter perturbation is less than 50%.
20. (Original) The method of claim 9, wherein the process chamber is an etching chamber.
21. (Original) The method of claim 9, wherein the process chamber is a deposition chamber.
22. (Original) The method of claim 9, further comprising:  
accessing a library of stored diagnosis information; and  
searching the diagnosis information to determine a solution to repair the identified fault.
23. (Original) Apparatus for evaluating a process chamber, comprising:  
an emission collector operatively coupled to a process chamber to measure emission from a plasma during a substrate processing operation and to produce emission data;  
an RF power monitoring circuit for monitoring voltage, current and phase of RF signals that are coupled to the process chamber and producing RF data; and

a computer processor, coupled to the emission collector, RF power monitoring circuit and the process chamber, for performing a multivariate analysis upon the emission data and the RF data.

24. (Original) The apparatus of claim 23, wherein the multivariate analysis comprises principle component analysis (PCA).

25. (Original) The apparatus of claim 23, wherein steady principle components and transitional principle components are identified for the process chamber by principle component analysis.

26. (Currently amended) The apparatus of claim 23, further comprising:  
a computer processor, coupled to the emission collector, RF power monitoring circuit, for enhancing [[the]] weak signals either by amplifying post perturbation signals, or by selecting a narrower and more sensitive wavelength range or frequency range.

27. (Original) The method of claim 1 further comprising using a result of the multivariate analysis to calibrate the process chamber or calibrate another process chamber.

28. (Original) The method of claim 1 further comprising using a result of the multivariate analysis to identify a fault in the process chamber or identify a fault in another process chamber.

29. (New) A method of evaluating a processing chamber, comprising:  
performing a substrate processing operation, followed by a process perturbation operation of the substrate process operation in the process chamber;  
collecting data of one or more plasma attributes during the substrate processing operation and the following process perturbation operation; and  
performing a multivariate analysis on the collected data of plasma attributes.

30. (New) The method of claim 29, wherein the one or more plasma attributes are selected from the group consisting of optical electromagnetic emission, RF power, wafer reflectance, process pressure, process temperature, and the combinations thereof.
31. (New) The method of claim 29, wherein the one or more plasma attributes are optical electromagnetic emission, RF power, and wafer reflectance.
32. (New) The method of claim 29, wherein the plasma attribute is wafer reflectance.
33. (New) The method of claim 29, wherein the multivariate analysis comprises principle component analysis (PCA).
34. (New) The method of claim 29, further comprising:  
determining if the data of plasma attributes need to be manipulated;  
performing data manipulation on the data of plasma attributes that are identified to need data manipulation; and  
performing a multivariate analysis on the revised data of plasma attributes.
35. (New) The method of claim 34, wherein steady principle components and transitional principle components are identified for the process chamber by principle component analysis.
36. (New) The method of claim 34, further comprising:  
using decomposition of a plasma attributes data matrix to yield scores of principle components to determine if the data of plasma attributes need to be manipulated.
37. (New) The method of claim 34, further comprising:  
enhancing weak signals either by amplification, or by selecting a narrower and more sensitive wavelength range or frequency range.

38. (New) The method of claim 29, further comprising:  
using a result of the multivariate analysis to identify a fault in the process chamber or to identify a fault in another process chamber.
39. (New) A method of evaluating a process chamber, comprising:  
performing a first substrate processing operation, followed by a first process perturbation operation of the first substrate process operation in a reference process chamber;  
collecting data of one or more plasma attributes during the substrate processing operation and the following first process perturbation operation in the reference process chamber;  
determining if the collected data of plasma attributes of the first process operation and the first process perturbation operation in the reference process chamber need to be manipulated;  
performing data manipulation on the data of plasma attributes of the reference chamber that are identified to need data manipulation;  
performing a multivariate analysis on the revised data of plasma attributes of the reference process chamber to produce first multivariate analysis results;  
performing a second substrate processing operation, followed by a second process perturbation operation of the first substrate process operation in a process chamber that is under study, wherein the first process operation and the second process operation are similar, and the first process perturbation operation and the second process perturbation operation are similar;  
collecting data of one or more plasma attributes during the second substrate processing operation and the following second process perturbation operation in the process chamber that is under study;  
performing data manipulation on the data of plasma attributes of the process chamber under study according to the data manipulation scheme used by the reference chamber;

performing a multivariate analysis on the revised data of plasma attributes of the process chamber under study to produce second multivariate analysis results;

comparing the second multivariate analysis results from the chamber under study to the first multivariate analysis results from the reference chamber.

40. (New) The method of claim 39, wherein the one or more plasma attributes are selected from the group consisting of optical electromagnetic emission, RF power, wafer reflectance, process pressure, process temperature, and the combinations thereof.

41. (New) The method of claim 39, wherein the one or more plasma attributes are optical electromagnetic emission, RF power, and wafer reflectance.

42. (New) The method of claim 39, wherein the plasma attribute is wafer reflectance.

43. (New) The method of claim 39 further comprising using a result of comparing the second multivariate analysis results to the first multivariate analysis results to calibrate the chamber under study.

44. (New) The method of claim 39, further comprising:  
using a result of comparing the second multivariate analysis results to the first multivariate analysis results to identify a fault in the chamber under study.

45. (New) The method of claim 39, wherein the first and second multivariate analyses comprise principle component analysis (PCA).

46. (New) The method of claim 45, wherein steady principle components and transitional principle components are identified for the reference chamber and the chamber under study by principle component analysis.



47. (New) The method of claim 39, wherein comparing the results from the first and second multivariate analyses further comprises performing an inner product of the identified principle components for the reference chamber and the chamber under study to generate matching scores.

48. (New) The method of claim 39, wherein determining if the collected data of plasma attributes need to be manipulated further comprising:

using decomposition of plasma attributes data matrixes for the reference chamber to yield scores for principle components to determine if the data of plasma attributes of the reference chamber need to be manipulated.

49. (New) The method of claim 39, wherein the performing data manipulation further comprising:

enhancing the weak signals either by amplification, or by selecting a narrower and more sensitive wavelength range or frequency range.

50. (New) The method of claim 47, further comprising:

comparing the matching scores to a pre-established matching control limit.

51. (New) The method of claim 39, wherein the first and second process perturbations are performed by varying at least one of the values of the process parameters.

52. (New) The method of claim 51, wherein the amount of process parameter variation is less than 50% of the un-perturbed process parameter.

53. (New) The method of claim 39, wherein the process chamber is an etching chamber.

54. (New) The method of claim 39, wherein the process chamber is a deposition chamber.

55. (New) The method of claim 44, further comprising:  
accessing a library of stored diagnosis information; and  
searching the diagnosis information to determine a solution to repair the identified fault.
56. (New) Apparatus for evaluating a process chamber, comprising:  
an optical electromagnetic emission and wafer reflectance collector coupled to a process chamber to collect optical electromagnetic emission data from a plasma and to collect wafer reflectance during a substrate processing operation;  
an RF power monitoring circuit for monitoring voltage, current and phase of RF signals that are coupled to the process chamber and producing RF data; and  
a computer processor, coupled to the optical electromagnetic emission and wafer reflectance collector, RF power monitoring circuit and the process chamber, for performing a multivariate analysis upon the emission data and the RF data.
57. (New) The apparatus of claim 56, wherein the multivariate analysis comprises principle component analysis (PCA).
58. (New) The apparatus of claim 56, further comprising:  
a computer processor coupled to the optical electromagnetic emission and wafer reflectance collector, and a RF power monitoring circuit for enhancing weak signals either by amplification, or by selecting a narrower and more sensitive wavelength range or frequency range.
59. (New) The apparatus of claim 56, further comprising:  
a light source, generating light from an excitation lamp or laser, coupled to the process chamber.

60. (New) The method of claim 29 further comprising using a result of the multivariate analysis to calibrate the process chamber or calibrate another process chamber.

61. (New) The method of claim 29 further comprising using a result of the multivariate analysis to identify a fault in the process chamber or identify a fault in another process chamber.